



# BYT 30PI-1000

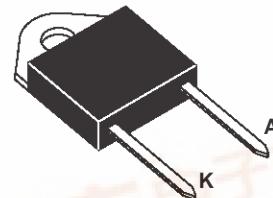
## FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED: Capacitance 15pF

### SUITABLE APPLICATIONS

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

Insulating voltage 2500 V<sub>RSM</sub>



Isolated  
DOP3I  
(Plastic)

### ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		1000	V
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage		1000	V
I <sub>FRM</sub>	Repetitive Peak Forward Current	t <sub>p</sub> ≤ 10μs	375	A
I <sub>F</sub> (RMS)	RMS Forward Current		70	A
I <sub>F</sub> (AV)	Average Forward Current	T <sub>c</sub> = 50°C δ = 0.5	30	A
I <sub>FSM</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	200	A
P	Power Dissipation	T <sub>c</sub> = 50°C	60	W
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 40 to +150	°C

### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th</sub> (j - c)	Junction-case	1.6	°C/W

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### ELECTRICAL CHARACTERISTICS

#### STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$I_R$	$T_j = 25^\circ C$	$V_R = V_{RRM}$			100	$\mu A$
	$T_j = 100^\circ C$				5	mA
$V_F$	$T_j = 25^\circ C$	$I_F = 30A$			1.9	V
	$T_j = 100^\circ C$				1.8	

#### RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
$t_{rr}$	$T_j = 25^\circ C$	$I_F = 1A$	$di_F/dt = -15A/\mu s$	$V_R = 30V$		165	ns
		$I_F = 0.5A$	$I_R = 1A$	$I_{rr} = 0.25A$		70	

#### TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$t_{IRM}$	$di_F/dt = -120A/\mu s$	$V_{CC} = 200V$ $I_F = 30A$			200	ns
	$di_F/dt = -240A/\mu s$	$L_p \leq 0.05\mu H$ $T_j = 100^\circ C$ See figure 11			120	
$I_{RM}$	$di_F/dt = -120A/\mu s$				19.5	A
	$di_F/dt = -240A/\mu s$				22	

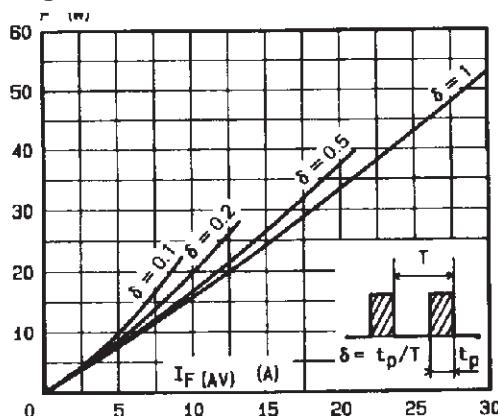
#### TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	$T_j = 100^\circ C$ $di_F/dt = -30A/\mu s$	$V_{CC} = 200V$ $L_p = 5\mu H$	$I_F = I_{F(AV)}$ See figure 12			4.5	

To evaluate the conduction losses use the following equations:

$$V_F = 1.47 + 0.010 I_F \quad P = 1.47 \times I_{F(AV)} + 0.010 I_{F(RMS)}^2$$

**Figure 1. Low frequency power losses versus average current**



**Figure 2. Peak current versus form factor**

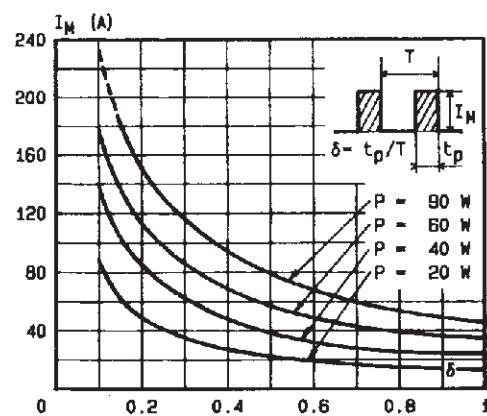


Figure 3. Non repetitive peak surge current versus overload duration

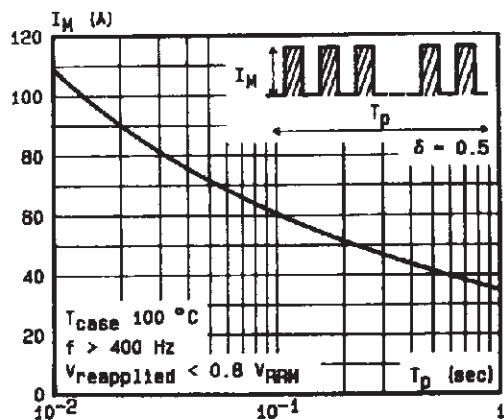


Figure 4. Thermal impedance versus pulse width

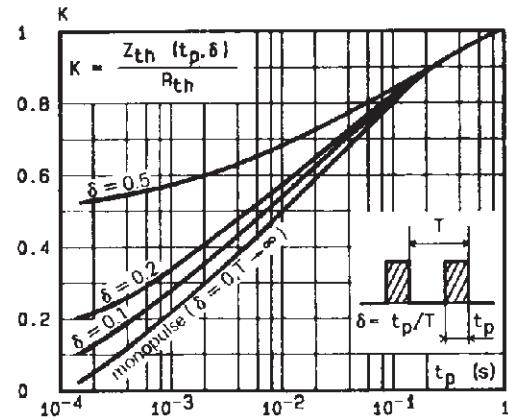


Figure 5. Voltage drop versus forward current

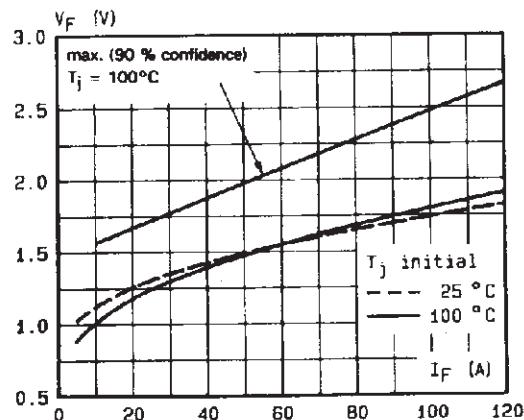


Figure 6. Recovery charge versus  $di_F/dt$

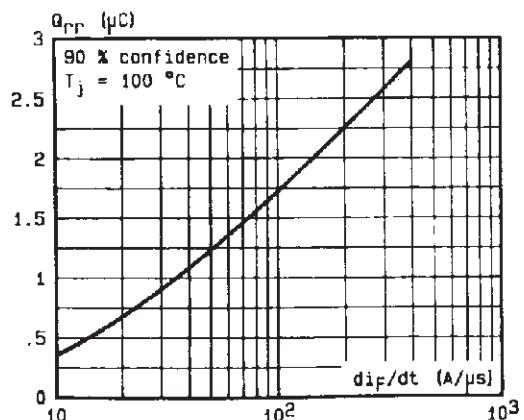


Figure 7. Recovery time versus  $di_F/dt$

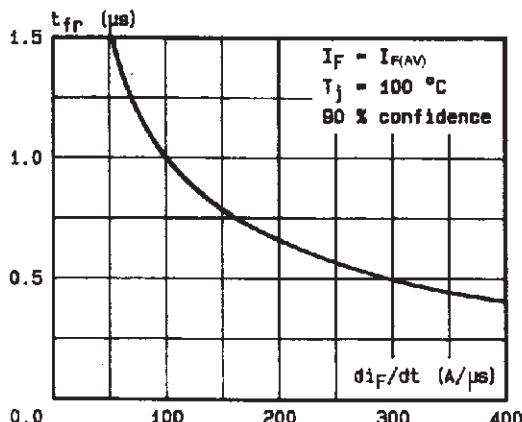
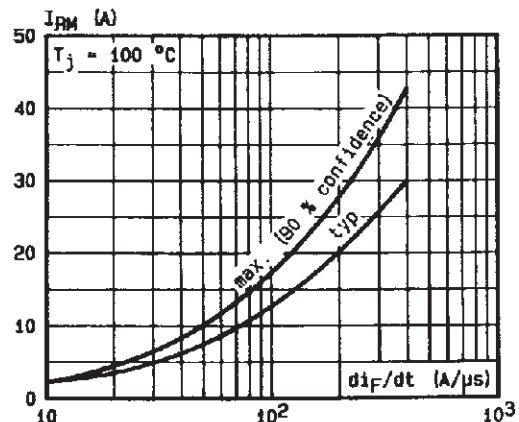


Figure 8. Peak reverse current versus  $di_F/dt$



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Figure 9. Peak forward voltage versus  $di_F/dt$ .

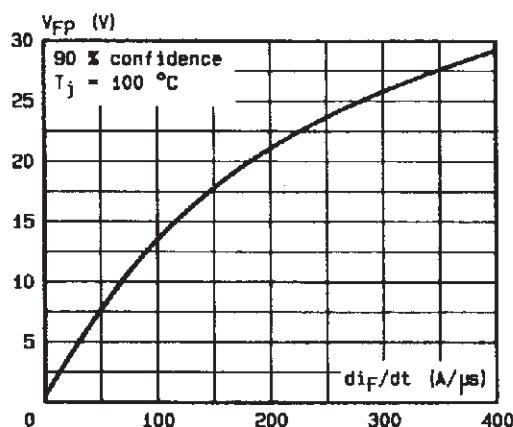


Figure 10. Dynamic parameters versus junction temperature.

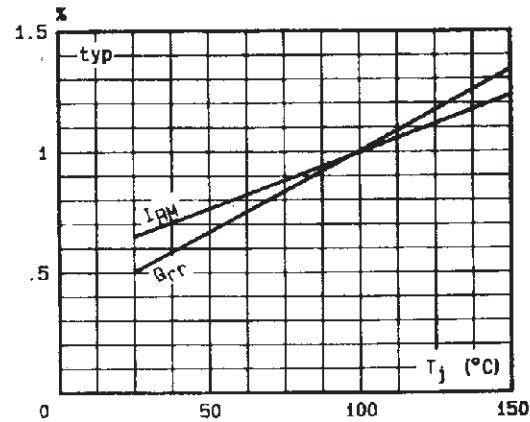


Figure 11. Turn-off switching characteristics (without series inductance).

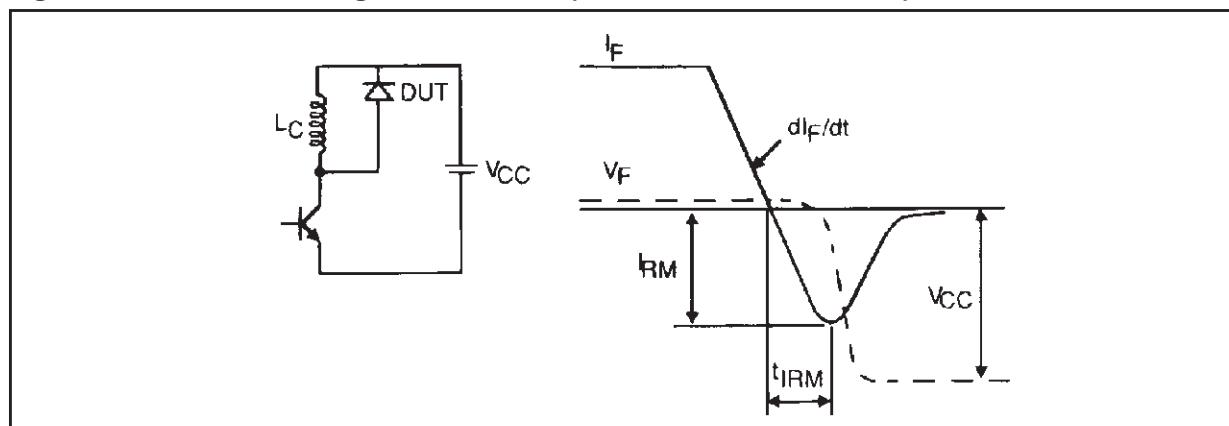
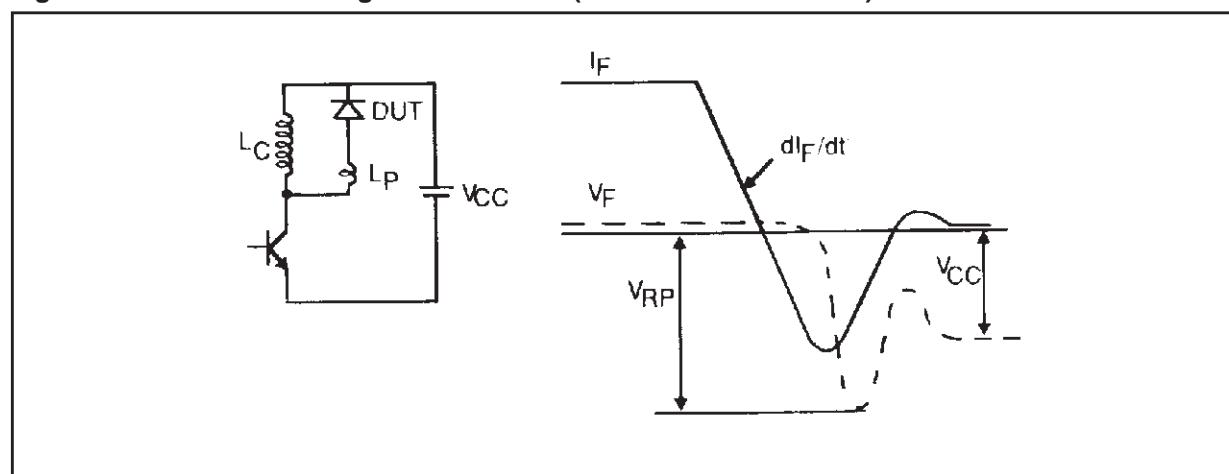


Figure 12. Turn-off switching characteristics (with series inductance)



## PACKAGE MECHANICAL DATA : Isolated DOP3I Plastic

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	1.45	1.55	0.057	0.061
C	14.35	15.60	0.565	0.614
D	0.5	0.7	0.020	0.028
E	2.7	2.9	0.106	0.114
F	15.8	16.5	0.622	0.650
G	20.4	21.1	0.815	0.831
H	15.1	15.5	0.594	0.610
K	3.4	3.65	0.134	0.144
L	4.08	4.17	0.161	0.164
N	10.8	11.3	0.425	0.444
P	1.20	1.40	0.047	0.055
R	4.60 typ.		0.181 typ.	

Cooling method: by conduction (method C)

Marking: type number

Weight: 18.84g

Recommended torque value: 250cm. N

Maximum torque value: 310cm. N

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